

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	(high near voltage near gate near dielectric) and (substrate or wafer) and (tri-gate) and (low near dose near3 nitrogen) and (low near voltage near core near dielectric) and (intermediate near core).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 18:26
L2	2	(high near voltage near gate near dielectric) and (substrate or wafer) and (tri-gate) and (low near dose near3 nitrogen) and (low near voltage near core near dielectric) and (intermediate near core)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 18:26